三、电容器电容的计算

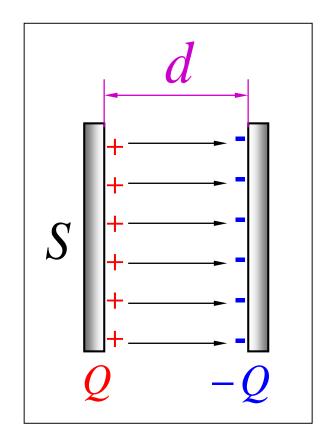
1. 平板电容器

两带电平板间的电场强度

$$E = \frac{\sigma}{\varepsilon_0} = \frac{Q}{\varepsilon_0 S}$$

两带电平板间的电势差

$$U = Ed = \frac{Qd}{\varepsilon_0 S}$$



平板电容器电容

$$C = \frac{Q}{U} = \frac{\varepsilon_0 S}{d}$$

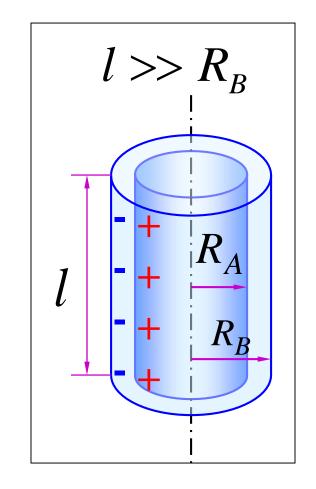
2. 圆柱形电容器

设两导体圆柱面单位长度上分别带电土入

$$E = \frac{\lambda}{2\pi \varepsilon_0 r}, \quad (R_A < r < R_B)$$

$$\Delta U = \int_{R_A}^{R_B} \frac{\lambda dr}{2\pi \varepsilon_0 r} = \frac{Q}{2\pi \varepsilon_0 l} \ln \frac{R_B}{R_A}$$

$$C = \frac{Q}{\Delta U} = \left(2\pi \varepsilon_0 l\right) / \ln \frac{R_B}{R_A}$$



3. 球形电容器的电容

球形电容器是由半径分别为 R_1 和 R_2 的两同心金 属球壳所组成.

解 设内球带正电(+Q),外球带负电(-Q).

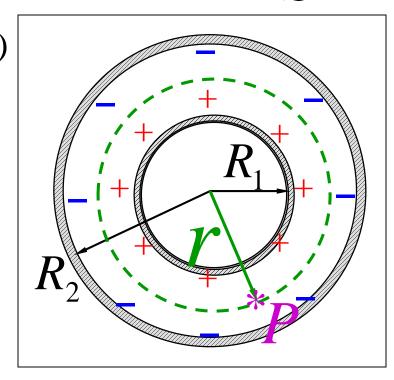
$$\vec{E} = \frac{Q}{4\pi \ \varepsilon_0 r^2} \vec{e}_r \quad (R_1 < r < R_2)$$

$$U = \int_{l} \vec{E} \cdot d\vec{l} = \frac{Q}{4\pi \varepsilon_{0}} \int_{R_{1}}^{R_{2}} \frac{dr}{r^{2}}$$
$$= \frac{Q}{4\pi \varepsilon_{0}} \left(\frac{1}{R_{1}} - \frac{1}{R_{2}}\right)$$

$$C = \frac{Q}{U} = 4\pi \varepsilon_0 \left(\frac{R_1 R_2}{R_2 - R_1}\right)$$

$$R_2 \to \infty, \quad C = 4\pi \varepsilon_0 R_1$$

$$R_2 \to \infty$$
, $C = 4\pi \ \varepsilon_0 R_1$



孤立导体球电容

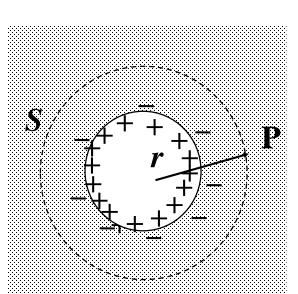
 $\boxed{\textbf{M} 1}$ 一导体带电球壳,带电q,周围充满无限大均匀介质,相对电容率为 ϵ_r ,求球外一点 \mathbb{P} 的场强、电势。

解:由于导体和介质都满足球对称性,故自由电荷和极化电荷分布也满足球对称性,因而电场的**分布**也具有球对称性。如图在介质中作一半径为r的球面S,根据 D的高斯定理:

$$\oint_{S} \vec{D} \cdot d\vec{S} = \sum q_{0} = q$$

$$D4\pi r^{2} = q, \quad D = \frac{q}{4\pi r^{2}}$$

$$\vec{D} = \varepsilon_{0} \varepsilon_{r} \vec{E}, \quad \vec{E} = \frac{\vec{D}}{\varepsilon_{0} \varepsilon_{r}} = \frac{q}{4\pi \varepsilon_{0} \varepsilon_{r} r^{2}} \hat{e}_{r}$$



$$U_{P} = \int_{P}^{\infty} \vec{E} \cdot d\vec{l} = \int_{r}^{\infty} \frac{q}{4\pi\varepsilon_{0}\varepsilon_{r}r^{2}} dr = \frac{q}{4\pi\varepsilon_{0}\varepsilon_{r}r}$$

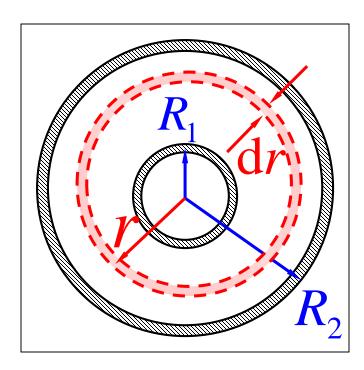
例2 如图所示,球形电容器的内、外半径分别为 R_1 和 R_2 , 所带电荷为 $\pm Q$ 。问此电容器贮存的电场能量 为多少?

解:
$$\vec{E} = \frac{1}{4\pi\varepsilon_0} \frac{Q}{r^2} \hat{e}_r \quad (R_1 > r > R_2)$$

$$dV = 4\pi r^2 dr$$

$$w_{\rm e} = \frac{1}{2} \varepsilon_0 E^2 = \frac{Q^2}{32 \pi^2 \varepsilon_0 r^4}$$

$$dW_{e} = w_{e}dV = \frac{Q^{2}}{8\pi\varepsilon_{0}r^{2}}dr$$



$$W_{\rm e} = \int dW_{\rm e} = \frac{Q^2}{8\pi \varepsilon_0} \int_{R_1}^{R_2} \frac{dr}{r^2}$$

$$= \frac{Q^2}{8\pi \varepsilon_0} \left(\frac{1}{R_1} - \frac{1}{R_2}\right) = \frac{1}{2} \frac{Q^2}{4\pi \varepsilon_0} \frac{Q^2}{R_2 R_1}$$

讨论:
$$W_{\rm e} = \frac{Q^2}{2 C}$$

$$C = 4\pi \ \varepsilon \frac{R_2 R_1}{R_2 - R_1}$$

——球形电容器电容